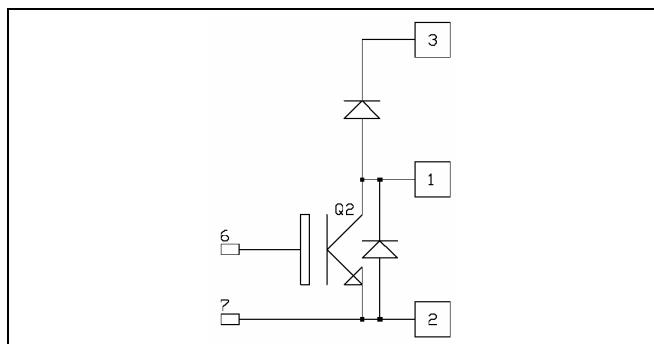


Boost Chopper NPT IGBT Power Module

**$V_{CES} = 600V$
 $I_C = 165A @ T_c = 80^\circ C$**



Application

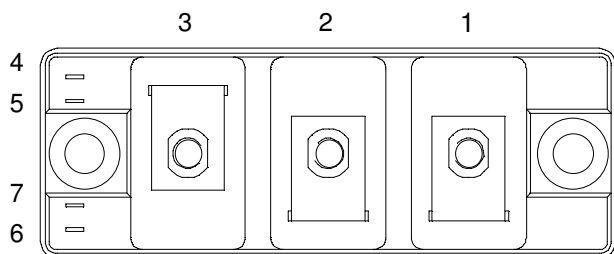
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of V_{CEsat}



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	A
		$T_C = 80^\circ C$	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	400
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	730
RBSOA	Reverse Bias Safe Operation Area	$T_j = 125^\circ C$	400A@420V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics
All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 5 \text{ mA}$	600			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$		1	500	μA
		$V_{CE} = 600V$		1		mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$		2.0	2.5	V
		$I_C = 200A$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4 \text{ mA}$	4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{MHz}$		9000		pF
C_{res}	Reverse Transfer Capacitance			800		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.5\Omega$		165		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			35		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.5\Omega$		180		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			285		
T_f	Fall Time			40		
E_{off}	Turn off energy			6.3		mJ

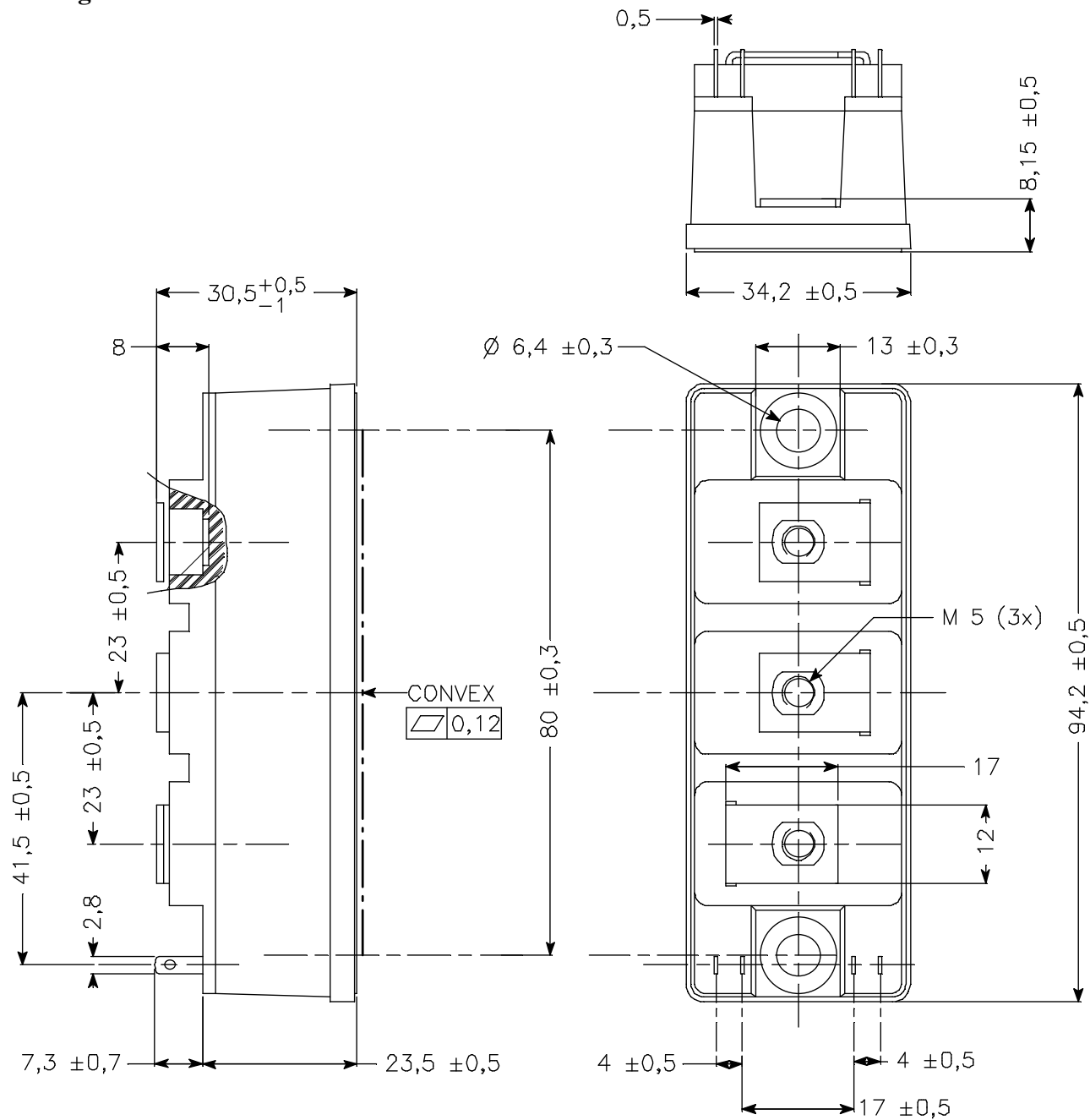
Reverse diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_F	Diode Forward Voltage	$I_F = 200A$		1.25	1.6	V
		$V_{GE} = 0V$		1.2		
E_r	Reverse Recovery Energy	$I_F = 200A$ $V_R = 300V$ $di/dt = 900A/\mu\text{s}$		4.1		mJ
Q_{rr}	Reverse Recovery Charge	$I_F = 200A$		12		μC
		$V_R = 300V$ $di/dt = 900A/\mu\text{s}$		19		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case		IGBT			0.17	°C/W
			Diode			0.29	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M5	2		3.5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					180	g

Package outline



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.